

Nch 800V 5A Power MOSFET

V_{DSS}	800V
R _{DS(on)} (Max.)	2.08Ω
I _D	5A
P_{D}	51W

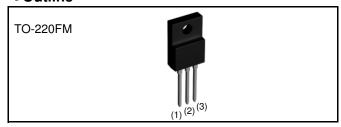
Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V $_{\mbox{\footnotesize GSS}})$ guaranteed to be $\pm 30\mbox{\rm V}.$
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

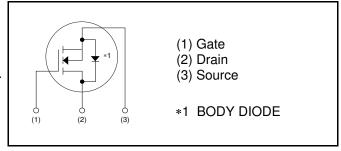
Application

Switching Power Supply

Outline



●Inner circuit



Packaging specifications

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	Packaging	Bulk			
Туре	Reel size (mm)	-			
	Tape width (mm)	-			
	Basic ordering unit (pcs)	500			
	Taping code	-			
	Marking	R8005ANX			

◆Absolute maximum ratings(T_a = 25°C)

Paramete	Symbol	Value	Unit	
Drain - Source voltage		V _{DSS}	800	V
Capting our during a green	T _c = 25°C	l _D *1	±5	Α
Continuous drain current	T _c = 100°C	l _D *1	±2.4	А
Pulsed drain current		I _{D,pulse} *2	±20	Α
Gate - Source voltage		V _{GSS}	±30	V
Avalanche energy, single pulse		E _{AS} *3	1.66	mJ
Avalanche energy, repetitive		E _{AR} *4	1.3	mJ
Avalanche current		I _{AR} *3	2.5	Α
Power dissipation $(T_c = 25^{\circ}C)$		P _D	51	W
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C
Reverse diode dv/dt		dv/dt *5	15	V/ns

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 640V, I_{D} = 5A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	UTIIL
Thermal resistance, junction - case	R_{thJC}	-	-	2.41	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	70	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

ullet Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	800	ı	1	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V, I_D = 2.5A$	ı	900	ı	V
Zero gate voltage drain current	I _{DSS}	V_{DS} = 800V, V_{GS} = 0V T_j = 25°C T_j = 125°C	-	0.1	100 1000	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	3	-	5	V
Static drain - source on - state resistance	R _{DS(on)} *6	$V_{GS} = 10V, I_D = 2.5A$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	-	1.60 3.69	2.08	Ω
Gate input resistance	R_{G}	f = 1MHz, open drain	-	7.7	-	Ω

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ainietei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_D = 2.5A$	1	2	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	485	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	250	-	рF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	21	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V	-	16.8	-	ņΕ
Effective output capacitance, time related	$C_{o(tr)}$	V _{DS} = 0V to 640V	-	41.2	-	pF
Turn - on delay time	t _{d(on)} *6	$V_{DD} \simeq 400V$, $V_{GS} = 10V$	-	17	-	
Rise time	t _r *6	$I_D = 2.5A$	-	17	-	no
Turn - off delay time	t _{d(off)} *6	$R_L = 160\Omega$	-	37	74	ns
Fall time	t _f *6	$R_G = 10\Omega$	-	41	82	

•Gate Charge characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*6}	$V_{DD} \simeq 400V$	-	21	ı	
Gate - Source charge	Q _{gs} *6	$I_D = 5A$	-	4.4	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	11	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 400V, I_D = 5A$	-	7.4	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} $P_W \le 10 \mu s$, Duty cycle $\le 1\%$

^{*3} L $^{\simeq}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C

^{*4} L $^{\sim}$ 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25°C	-	1	5	А
Inverse diode direct current, pulsed	I _{SM} *2	1 c = 25 0	-	-	20	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_{S} = 5A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	554	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 5A di/dt = 100A/μs	-	4.6	-	μС
Peak reverse recovery current	I _{rrm} *6		-	16.5	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C	-	30	-	A/μs

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	0.258	
R _{th2}	0.966	K/W
R _{th3}	2.18	

Symbol	Value	Unit
C _{th1}	0.00169	
C _{th2}	0.0194	Ws/K
C _{th3}	0.461	

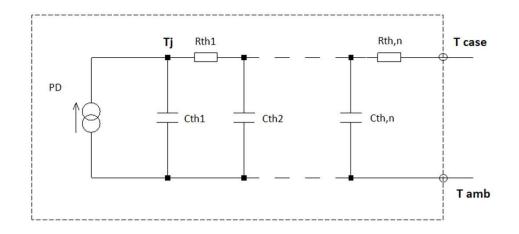
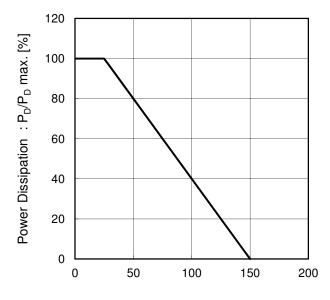
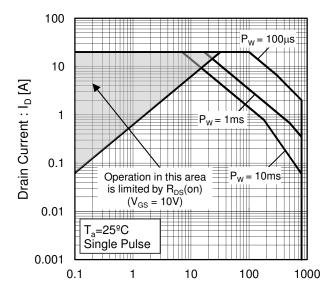


Fig.1 Power Dissipation Derating Curve

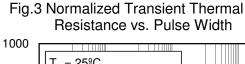


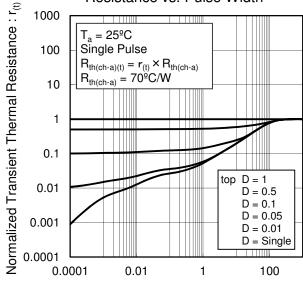
Junction Temperature : T_i [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]





Pulse Width: Pw [s]

Fig.4 Avalanche Current vs Inductive Load

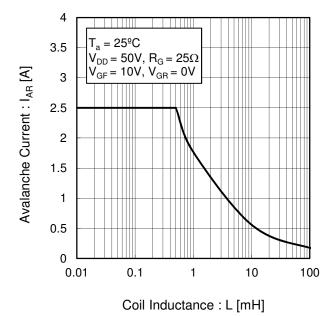
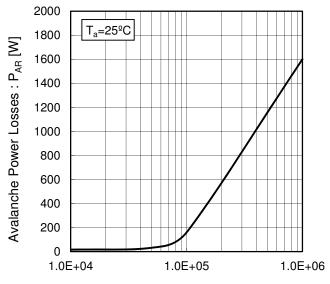
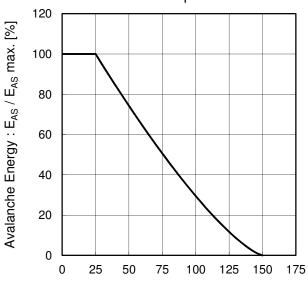


Fig.5 Avalanche Power Losses



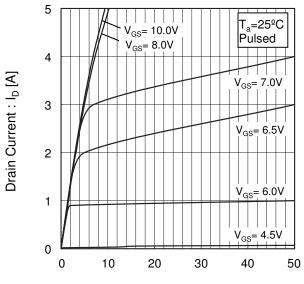
Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs Junction Temperature



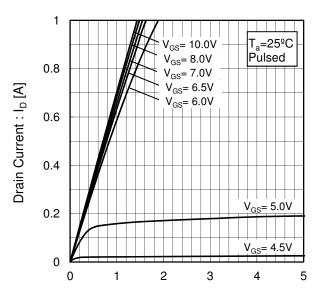
Junction Temperature : T_i [°C]

Fig.7 Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

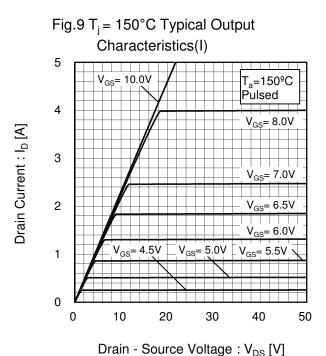
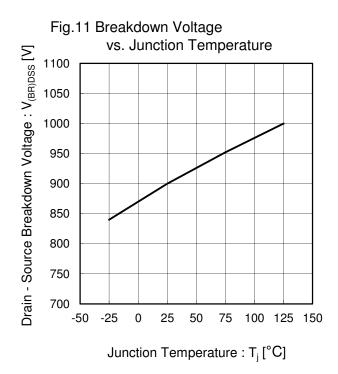


Fig.10 $T_j = 150$ °C Typical Output Characteristics(II) $V_{GS} = 10.0V$ T_a=150ºC $V_{GS} = 8.0V$ $V_{GS} = 7.0V$ Pulsed 8.0 $V_{GS} = 6.5V$ Drain Current : I_D [A] V_{GS}= 6.0V $V_{GS} = 5.5V$ 0.6 V_{GS}= 5.0V 0.4 0.2 $V_{GS} = 4.5V$ 0 2 3 0 1 5 4

Drain - Source Voltage : V_{DS} [V]



10 V_{DS}= 10V Plused 1 Drain Current : I_D [A] 0.1 ເ_a=75ºC a=25ºC 0.01 -25ºC 0.001 3.0 4.0 5.0 6.0 7.0 9.0 2.0

Gate - Source Voltage : V_{GS} [V]

Fig.12 Typical Transfer Characteristics

Fig.13 Gate Threshold Voltage vs. Junction Temperature 6 V_{DS}= 10V Plused Gate Threshold Voltage : $V_{GS(th)}\left[V\right]$ 5 3 2 -25 100 125 150 -50 0 25 50 75 Junction Temperature : T_i [°C]

10 | V_{DS}= 10V | Plused | T_a= -25°C | T_a=25°C | T_a=75°C | T_a=125°C | T_a=

Drain Current : I_D [A]

Fig.14 Transconductance vs. Drain Current

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Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

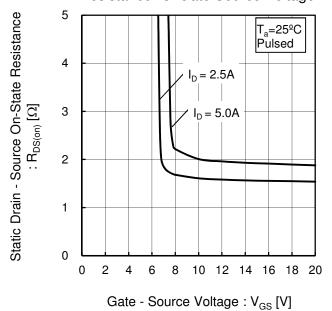
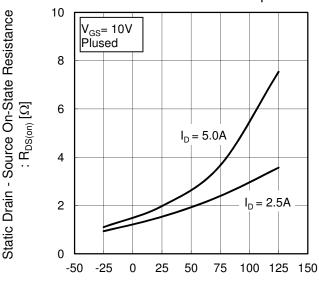
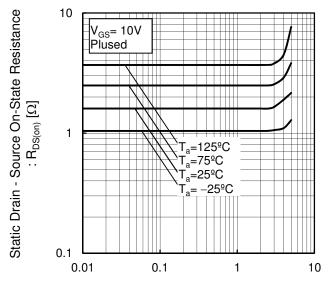


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_i [${}^{\circ}C$]

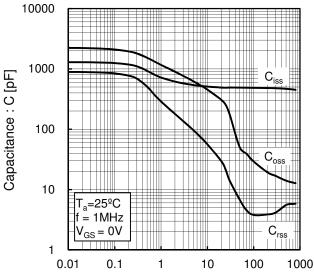
Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current : I_D [A]

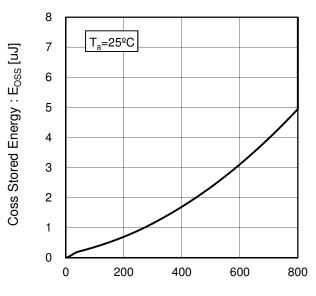
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Fig.18 Typical Capacitance
vs. Drain - Source Voltage



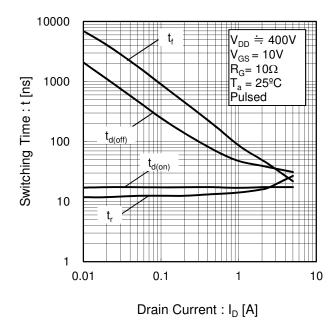
Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy



Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics



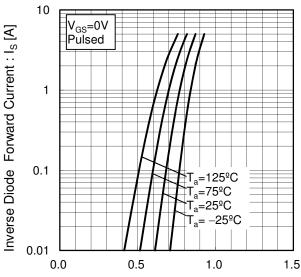
Gate - Source Voltage : $V_{GS}\left[V\right]$

12 10 8 6 4 $T_a = 25^{\circ}C$ $V_{DD} = 400V$ $I_D = 5A$ 2 Pulsed 0 5 0 10 15 25 30 20

Fig.21 Dynamic Input Characteristics

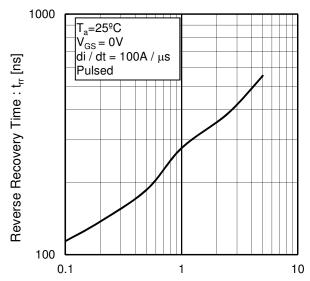
Total Gate Charge : Q_q [nC]

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

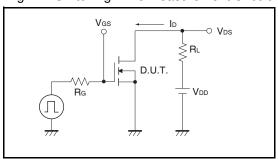


Fig.2-1 Gate Charge Measurement Circuit

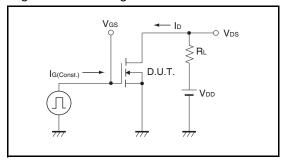


Fig.3-1 Avalanche Measurement Circuit

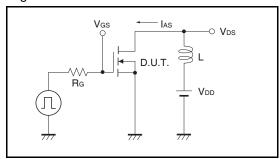


Fig.4-1 dv/dt Measurement Circuit

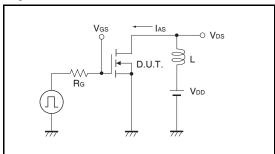


Fig.5-1 di/dt Measurement Circuit

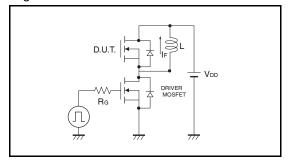


Fig.1-2 Switching Waveforms

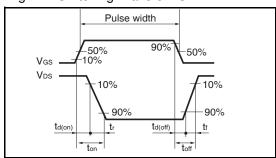


Fig.2-2 Gate Charge Waveform

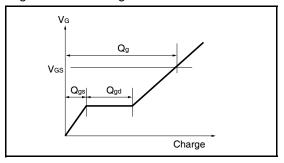


Fig.3-2 Avalanche Waveform

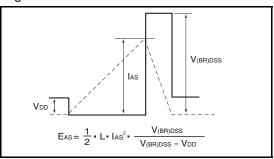


Fig.4-2 dv/dt Waveform

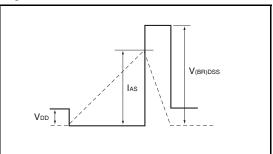
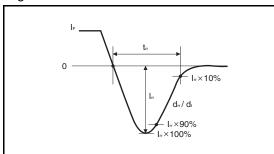
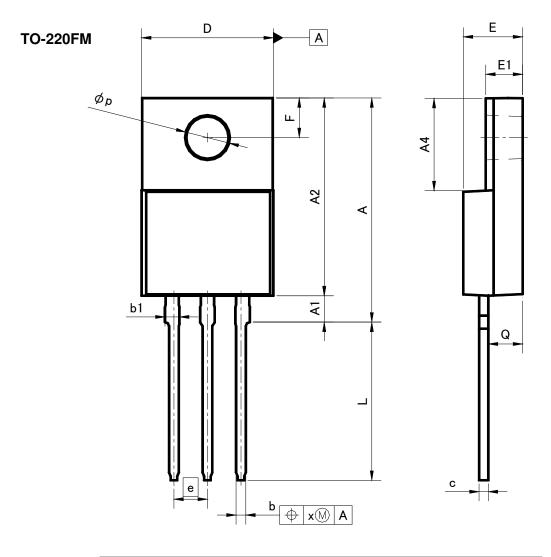


Fig.5-2 di/dt Waveform



● **Dimensions** (Unit: mm)



DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
Е	4.40	4.80	0.173	0.189
е	2.	54	0.1	00
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
х	_	0.38	_	0.015

Dimension in mm / inches

Notice

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(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSⅢ	CLASSII	CLASS II b	CLASSIII
CLASSIV		CLASSⅢ	

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 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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